

# MSN30H12D(MSN0530D)

# **Preliminary Datasheet**

# N-Channel 30-V (D-S) MOSFET

### **FEATURES**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

PRODUCTY SUMMARY					
V <sub>DS</sub>	R	$_{DS(on)} m(\Omega)$	I <sub>D</sub> (A)		
30	6.0	Rdson @10V	20		
	7.6	Rdson @4.5V	19		

# **Application**

- Portable Devices
- ■Consumer Electronics

## Mechanical

●Case: TO-252 Package

# **Packing Information**

Package	Packing		
TO-252	2.5K/13" Reel		



TO-252

Maximo	um Ratings (T <sub>A</sub> =25°C unle	ess otherwise sp	ecified)	
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current (Note 4)	TC=25°C	I <sub>D</sub>	20	А
Pulsed Drain Current (Note 1)	TC=25°C	I <sub>DM</sub>	80	А
Power Dissipation	TC=25°C	P <sub>D</sub>	3.2	W
	Typical Thermal Ro	esistance		·
Parameter		Symbol	Limit	Unit
Junction-to-Ambient Thermal Resistance	Junction to Case	R <sub>eJC</sub>	1.39	°C/W

### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.

 $R_{\theta,JA}$ 

100

4. The maximum current rating is package limited.

Junction-to-Ambient Thermal Resistance

5. RQJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.

Junction to Ambient

- 6. The test condition is L=0.1mH,  $I_{AS}$ =40A,  $V_{DD}$ =25V,  $V_{GS}$ =10V.
- 7. Guaranteed by design, not subject to production testing.

°C/W



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Electrical Characteristics (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Characteristics	Coursels of	Took Condition	Limits			11	
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	B <sub>VDSS</sub>	$VGS = 0V, I_D = 250uA$	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	VDS=VGS, I <sub>D</sub> =250uA	1	1.55	2.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10.0V, I <sub>D</sub> =20.0A	-	4.0	6.0	mΩ	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =19.0A	-	5.0	7.6	mΩ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	VDS=30V, VGS=0V	-	-	1.0	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA	
		Dynamic <sup>3)</sup>					
Total Gate Charge	$Q_g$	\/ 45\/ L 20A	-	12	-	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =15V, $I_{D}$ =20A, $V_{GS}$ =4.5 (Note 2,3)	-	3.8	-	nC	
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> -4.5	-	4.3	-	nC	
Input Capacitance	C <sub>iss</sub>		-	1323	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =25V, $V_{GS}$ =0V, f=1.0MHZ	-	219	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1=1.011112	-	136	-	pF	
		Switching					
Turn-On Delay Time	$t_{d(on)}$	\/D0-45\/ DL-40	-	5	-	ns	
Turn-On Rise Time	t <sub>r</sub>	VDS=15V, RL=1Ω, VGS=10V, RG=3.3Ω	-	42	-	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	(Note 2,3)	-	36	-	ns	
Turn-Off Fall Time	t <sub>f</sub>		-	5.5	-	ns	
Drain-Source Diode							
Maximum Continuous Body Diode Forward Current	I <sub>S</sub>	-	-	-	1.2	Α	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	-	1.5	V	

# Note:

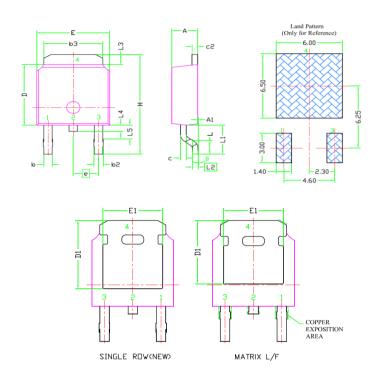
- 1. Pulse width<300us, Duty cycle<2%
- Fused current that based on wire numbers and diameter
  Guaranteed by design, not subject to production testing.



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## Package Outline Dimensions (inches and millimeters)

TO-252					
	Dimensions				
SYMBOL	Millimeters		Inches		
	Min	Max	Min	Max	
E	6.40	6.73	0.252	0.265	
L	1.40	1.77	0.055	0.070	
L1	2.743 REF				
L2	0.508BSC				
L3	0.89	1.27	0.035	0.050	
L4	0.64	1.01	0.025	0.040	
L5	-	-	=	-	
D	6.00	6.22	0.236	0.245	
Н	9.40	10.40	0.370	0.409	
b	0.64	0.88	0.025	0.035	
b2	0.77	1.14	0.030	0.045	
b3	5.21	5.46	0.205	0.215	
е	2.286BSC				
Α	2.20	2.38	0.087	0.094	
A1	0.00	0.13	0.000	0.005	
С	0.46	0.60	0.018	0.024	
c2	0.46	0.58	0.018	0.023	
D1	5.21		0.205	-	
E1	4.40	-	0.173	-	
Θ	0 °	10 °	0 °	10 °	



# **Marking Information**



First line:

AAAAAAAA = Product number

XXXXXXX = Tracking number

Third line:Gate Pin Point

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